

**ECSE-2210 Microelectronics Technology**  
**Homework 3 – Solution**

1. At thermal equilibrium,  $np \approx n_i^2$

At 300 K,  $n = 10^{17} \text{ cm}^{-3}$ ,  $n_i = 10^{10} \text{ cm}^{-3}$ ,  $p = 10^3 \text{ cm}^{-3}$

At 200 K,  $n = 10^{17} \text{ cm}^{-3}$ ,  $n_i = 10^5 \text{ cm}^{-3}$ ,  $p = 10^{-7} \text{ cm}^{-3}$

That is, the hole concentration at 200 K is extremely small. You will find only one hole in a volume of  $10^7 \text{ cm}^3$  of Si !

2. a) At room temperature in Si,  $n_i = 10^{10} \text{ cm}^{-3}$ . Thus here  $N_D \gg N_A$ ,  $N_D \gg n_i$  and  $n = N_D = 10^{15} \text{ cm}^{-3}$

$$p = n_i^2 / N_D = 10^5 \text{ cm}^{-3}$$

- b) Since  $N_D \ll N_A$ ,  $N_A \gg n_i$

$$p = N_A = 10^{16} \text{ cm}^{-3}$$

$$n = n_i^2 / N_A = 10^4 \text{ cm}^{-3}$$

- c) Here we must retain both  $N_D$  and  $N_A$ , but  $N_D - N_A \gg n_i$

$$n = N_D - N_A = 10^{15} \text{ cm}^{-3}$$

$$p = n_i^2 / (N_D - N_A) = 10^5 \text{ cm}^{-3}$$

- d) We deduce from Figure 2.20 that, at 450 K,  $n_i \text{ (Si)} \approx 5 \times 10^{13} \text{ cm}^{-3}$ . Clearly,  $n_i$  is comparable to  $N_D$  and we must use Eq. 2.29a

$$n = N_D / 2 + [(N_D / 2) + n_i^2]^{1/2} = 1.21 \times 10^{14} \text{ cm}^{-3}$$

$$p = n_i^2 / n = 2.07 \times 10^{13} \text{ cm}^{-3}$$

e) We conclude from figure 2.20, that at 650 K,  $n_i = 10^{16} \text{ cm}^{-3}$  Here  $n_i \gg N_D$

$$p = n_i = 10^{16} \text{ cm}^{-3}$$

$$n = n_i = 10^{16} \text{ cm}^{-3}$$

3)

(i) As established in the text [Eq.(2.36)],

$$E_i = \frac{E_c + E_v}{2} + \frac{3}{4} kT \ln(m_p^*/m_n^*)$$

Taking  $m_p^*/m_n^*$  to be temperature independent and employing the values listed in Table 2.1, one concludes

part	T(K)	kT (eV)	$E_i$ displacement from midgap (eV)
(a-c)	300	0.0259	-0.0073
(d)	450	0.0388	-0.0109
(e)	650	0.0560	-0.0158

Alternatively, the  $m_p^*/m_0$  and  $m_n^*/m_0$  versus  $T$  fit-relationships cited in Exercise 2.4 may be used to compute the  $m_p^*/m_n^*$  ratio. One finds

part	T(K)	$m_p^*/m_n^*$	kT (eV)	$E_i$ displacement from midgap (eV)
(a-c)	300	0.680	0.0259	-0.0075
(d)	450	0.703	0.0388	-0.0103
(e)	650	0.719	0.0560	-0.0139

(ii)  $E_F - E_i$  is computed using the appropriate version of Eq.(2.37) or (2.38).

(a)  $E_F - E_i = kT \ln(N_D/n_i) = 0.0259 \ln(10^{15}/10^{10}) = 0.298 \text{ eV}$

(b)  $E_i - E_F = kT \ln(N_A/n_i) = 0.0259 \ln(10^{16}/10^{10}) = 0.358 \text{ eV}$

(c)  $E_F - E_i = kT \ln[(N_D - N_A)/n_i] = 0.0259 \ln(10^{15}/10^{10}) = 0.298 \text{ eV}$

(d)  $E_F - E_i = kT \ln(n/n_i) = 0.0388 \ln(1.21 \times 10^{14}/5 \times 10^{13}) = 0.034 \text{ eV}$

(e)  $E_F - E_i = kT \ln(n/n_i) \equiv 0 \quad \dots (n \equiv n_i)$

